

L Number	Hits	Search Text	DB	Time stamp
1	573	(438/10).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/12 11:32
2	318	(438/421).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/12 11:32
-	1290400	silicon adj wafer or semiconductor wafer or wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:30
-	10673	vacuum adj chuck or wafer adj holder	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 14:30
-	8861	(silicon adj wafer or semiconductor wafer or wafer) and (vacuum adj chuck or wafer adj holder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 14:30
-	1842	diffusion adj barrier and gold	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 14:48
-	30	((silicon adj wafer or semiconductor wafer or wafer) and (vacuum adj chuck or wafer adj holder)) and (diffusion adj barrier and gold)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 14:31
-	16964	conductive adj contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 14:50
-	50	((silicon adj wafer or semiconductor wafer or wafer) and (vacuum adj chuck or wafer adj holder)) and (conductive adj contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:00
-	0	"silicon coated wafer holder" or "silicon coated chuck" or "silicon coated wafer chuck"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:01
-	0	"silicon coated fingers"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:09
-	915386	coated adj chuck or coated wafer adj chuck	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:32
-	811	(diffusion adj barrier and gold) and (coated adj chuck or coated wafer adj chuck)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:10
-	25	(conductive adj contact) and ((diffusion adj barrier and gold) and (coated adj chuck or coated wafer adj chuck))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:18

-	1469	silicon adj coated	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:19
-	14	(vacuum adj chuck or wafer adj holder) and (silicon adj coated)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:19
-	566829	bias or biased	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:30
-	1290410	silicon adj wafer or semiconductor wafer or wafer or suseptor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:44
-	1699	(bias or biased) near (silicon adj wafer or semiconductor wafer or wafer or suseptor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:32
-	912136	coated adj chuck or coated wafer adj chuck and ((bias or biased) near (silicon adj wafer or semiconductor wafer or wafer or suseptor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:32
-	359	(coated adj chuck or coated wafer adj chuck) and ((bias or biased) near (silicon adj wafer or semiconductor wafer or wafer or suseptor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:33
-	1294667	silicon adj wafer or semiconductor wafer or wafer or susceptor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:45
-	1719	(bias or biased) near (silicon adj wafer or semiconductor wafer or wafer or susceptor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:45
-	359	((coated adj chuck or coated wafer adj chuck) and ((bias or biased) near (silicon adj wafer or semiconductor wafer or wafer or suseptor))) and ((bias or biased) near (silicon adj wafer or semiconductor wafer or wafer or susceptor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 15:59
-	0	"semiconductor coated susceptor"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 16:00
-	7	"silicon coated susceptor"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 16:07
-	5	5324685.URPN.	USPAT	2003/01/20 16:05
-	0	6022587.URPN.	USPAT	2003/01/20 16:05

-	24	("4764394"   "4808546"   "4933063"   "5032202"   "5183775"   "5196355"   "5289010"   "5296272"   "5304279"   "5305221"   "5311028"   "5342652"   "5380682"   "5427638"   "5436175"   "5525159"   "5554249"   "5554853"   "5580429"   "5641707"   "5653811"   "5661043"   "5711812"   "5854123").PN.	USPAT	2003/01/20 16:05
-	931	"remove native oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 08:47
-	1296714	backside or rear	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 16:08
-	147	"remove native oxide" and (backside or rear)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:43
-	2	("6251242").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 16:12
-	1	6217724.URPN.	USPAT	2003/01/20 17:01
-	7	("4579609"   "5134301"   "5292393"   "5653811"   "5654043"   "6028285"   "6120660").PN.	USPAT	2003/01/20 17:03
-	5	silicon adj platen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:10
-	99	"johnsen-rahbek"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:13
-	0	"silicon coated electrostatic chuck"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:18
-	0	"semiconductor coated electrostatic chuck"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:18
-	0	"semiconductor coated chuck"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:19
-	0	"semiconductor coated platen"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:23
-	6	("5384682"   "5663865"   "5708557"   "5909354"   "5969934"   "6122159").PN.	USPAT	2003/01/20 17:20
-	0	"semiconductor covered platen"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:24

-	0	"semiconductor covered chuck"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:25
-	0	"silicon covered chuck"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:25
-	0	"silicon covered platen"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:25
-	0	"silicon covered sesceptor"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:25
-	0	"semiconductor covered sesceptor"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/20 17:25
-	0	"remove native oxide" near (backside or rear)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:46
-	5	"remove native oxide" near (backside or rear or bottom or "both sides")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:49
-	0	"etching the bottom of the wafer" or "etching the bottom of the semiconductor wafer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 10:50
-	4962	native adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 13:42
-	0	"rear side of wafer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 13:42
-	46520	"wafer bottom" or "wafer rear side" or "rear side of wafer" or backside	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 13:44
-	510	(native adj oxide) and ("wafer bottom" or "wafer rear side" or "rear side of wafer" or backside)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/24 13:44
-	1	6444027.URPN.	USPAT	2003/07/30 08:09
-	15	("4322592"   "4496609"   "5192371"   "5200157"   "5242501"   "5516367"   "5679405"   "5769942"   "5856240"   "5904769"   "5960555"   "6103014"   "6127286"   "6129047"   "6184154").PN.	USPAT	2003/07/30 08:10
-	2583	bias near7 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:12

-	955	(chuck or susceptor or holder) and (bias near7 wafer )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:12
-	56	"remove native oxide" and ((chuck or susceptor or holder) and (bias near7 wafer ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 08:13
-	2	("6217724").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 10:11
-	2	6217724.URPN.	USPAT	2003/07/30 10:11
-	7	("4579609"   "5134301"   "5292393"   "5653811"   "5654043"   "6028285"   "6120660").PN.	USPAT	2003/07/30 10:12
-	155	memory adj device and probe and (test adj mosfet or test and transistor or test adj memory adj device or test adj circuit) and needle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 15:06
-	133	(memory adj device and probe and (test adj mosfet or test and transistor or test adj memory adj device or test adj circuit) and needle) and (wafer or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 15:10
-	46	source and drain and ((memory adj device and probe and (test adj mosfet or test and transistor or test adj memory adj device or test adj circuit) and needle) and (wafer or substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 15:10
-	606	"memc electronic materials"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 15:33
-	90	back adj surface and "memc electronic materials"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 15:39
-	0	00034999.pct	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 15:39
-	0	021198.pct	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 15:39
-	285	(117/200).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 16:21
-	119396	wafer adj holder or chuck or susceptor or substrate adj holder	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 16:22
-	0	((117/200).CCLS.) near electrically adj connected	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 16:23

-	0	((117/200).CCLS.) near (bias or biased)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:23
-	0	((117/200).CCLS.) near electrically adj connected) near electrically adj connected	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:23
-	0	((117/200).CCLS.) near electrically adj connected) near (bias or biased)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:23
-	314	(wafer adj holder or chuck or susceptor or substrate adj holder) near (bias or biased)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:29
-	0	autodoping and ((wafer adj holder or chuck or susceptor or substrate adj holder) near (bias or biased))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:29
-	0	(autodoping or auto adj doping) and ((wafer adj holder or chuck or susceptor or substrate adj holder) near (bias or biased))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:29
-	1237	(autodoping or auto adj doping)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:30
-	201	(wafer adj holder or chuck or susceptor or substrate adj holder) and ((autodoping or auto adj doping) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:34
-	9	"electrically connected" and ((wafer adj holder or chuck or susceptor or substrate adj holder) and ((autodoping or auto adj doping) ))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:34
-	91	"electrically connected" near (wafer adj holder or chuck or susceptor or substrate adj holder)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:36
-	0	((autodoping or auto adj doping) ) and ("electrically connected" near (wafer adj holder or chuck or susceptor or substrate adj holder))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:35
-	1939037	back or rear near5 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:37
-	26	("electrically connected" near (wafer adj holder or chuck or susceptor or substrate adj holder)) and (back or rear near5 wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/30 16:37
-	37	wafer adj bias and native adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/31 08:45

-	2529	electrical adj contact near (wafer or semiconductor adj wafer or substrate or semiconductor adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/31 08:46
-	15	"remove native oxide" and (electrical adj contact near (wafer or semiconductor adj wafer or substrate or semiconductor adj substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/31 08:47